SC1188

Programmable Synchronous DC/DC Converter, Dual Low Dropout Regulator Controller

Description

The SC1188 combines a synchronous voltage mode controller with two low-dropout linear regulators providing most of the circuitry necessary to implement three DC/DC converters for powering advanced, low cost microprocessors.

The SC1188 switching section features an integrated 4 bit D/A converter, latched drive output for enhanced noise immunity and pulse by pulse current limiting. The SC1188 switching section operates at a fixed frequency of 200kHz, providing an optimum compromise between size, efficiency and cost in the intended application areas. The integrated D/A converter provides programmability of output voltage from 1.30V to 2.05V in 50mV increments with no external components.

The SC1188 linear sections are low dropout regulators with short circuit protection, supplying 1.8V for Bridge and 2.5V for non-GTL I/O.

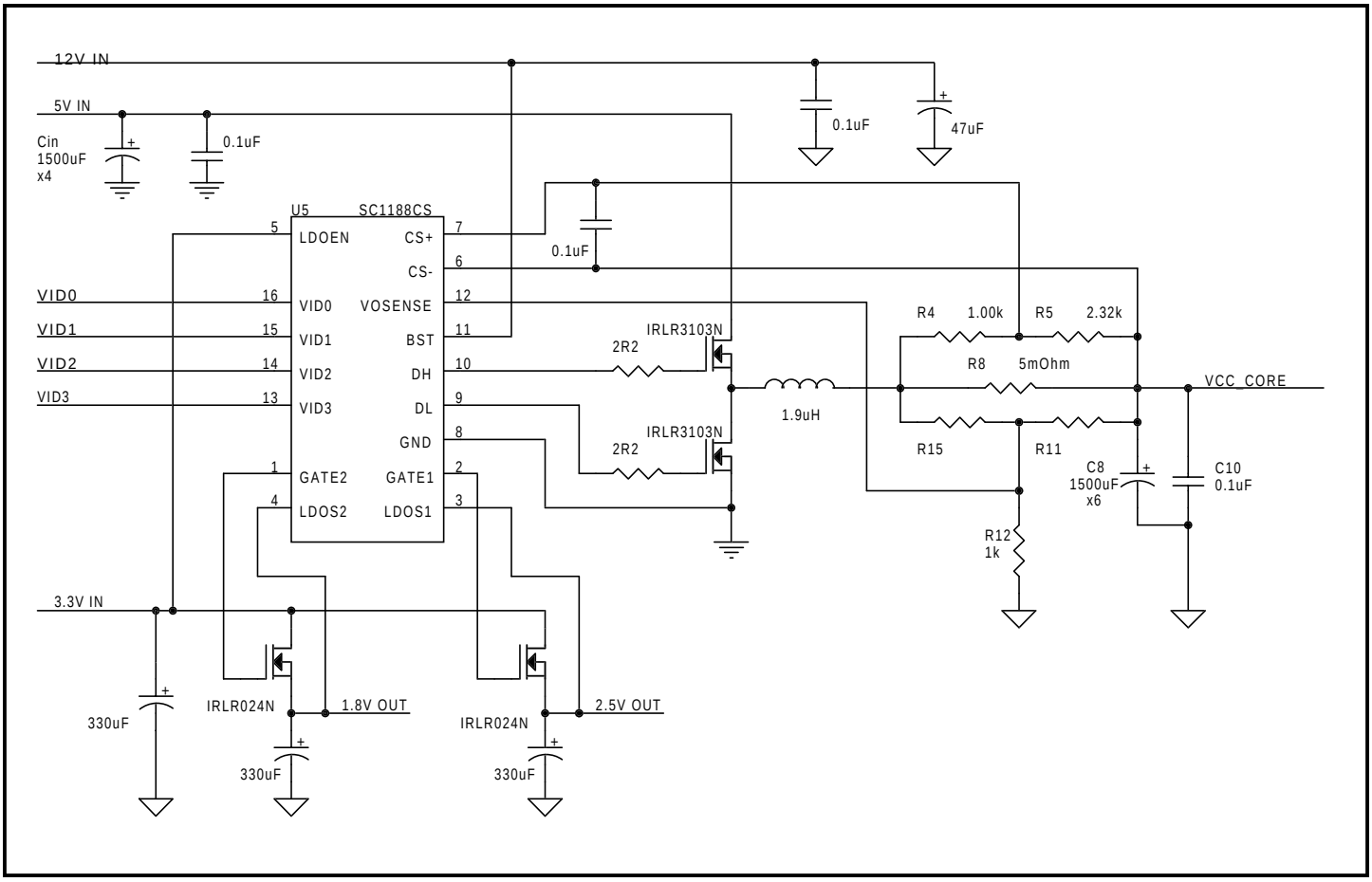
Features

- Synchronous design, enables no heatsink solution
- 95% efficiency (switching section)
- 4 bit DAC for output programmability
- 1.8V, 2.5V short circuit protected linear controllers
- VRM8.4 Compliant

Applications

- Low Cost Motherboards
- 1.3V to 2.05V microprocessor supplies
- Programmable triple power supplies

Typical Application Circuit



Absolute Maximum Ratings

Parameter	Symbol	Maximum	Units
BST to GND		-0.3 to +15	V
VOSENSE and LDOEN to GND		-0.3 to +7	V
VIDx to GND		-0.3 to +5.5	V
LDOSx		-0.3 to BST+0.3	V
Operating Temperature Range	T_A	0 to +70	°C
Junction Temperature Range	T_J	0 to +125	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C
Lead Temperature (Soldering) 10 Sec.	T_{LEAD}	300	°C
Thermal Resistance Junction to Ambient	θ_{JA}	130	°C/W
Thermal Impedance Junction to Case	θ_{JC}	30	°C/W

NOTE:
(1) This device is ESD sensitive. Use of standard ESD handling precautions is required.

Electrical Characteristics

Unless otherwise specified: LDOEN = 3.3V; VOSENSE = V_O; 0mV < (CS+-CS-) < 60mV; BST = 11.4V to 12.6V; T_A = 0 to 70°C

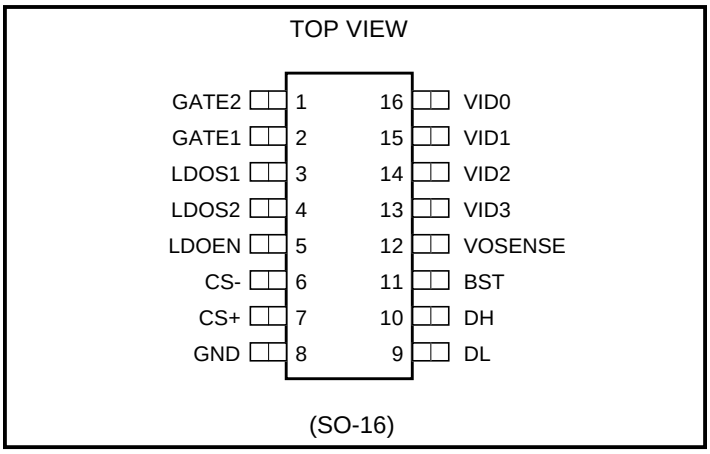
Parameter	Conditions	Min	Typ	Max	Units
Switching Section					
Output Voltage	IO = 2A in Application Circuit	See Output Voltage Table			
Load Regulation	IO = 0.8A to 15A		1		%
Line Regulation			±0.15		%
Current Limit Voltage		60	70	85	mV
Oscillator Frequency		175	200	225	kHz
Oscillator Max Duty Cycle		90	95		%
Peak DH Sink/Source Current	BSTH - DH = 4.5V, DH- PGNDH = 3.1V DH- PGNDH = 1.5V	500 100			mA mA
Peak DL Sink/Source Current	BSTL - DL = 4.5V, DL - PGNDL= 3.1V DL- PGNDH = 1.5V	500 100			mA mA
Gain (AOL)	VOSENSE to VO		35		dB
VID Source Current	VIDx < 2.4V	1	10		µA
VID Leakage	VIDx = 3.3V			10	µA
Dead time		40	100		ns

Electrical Characteristics (Cont.)

Unless specified: LDOEN = 3.3V; VOSENSE = V_O; 0mV < (CS+-CS-) < 60mV; BST = 11.4V to 12.6V; T_A = 0 to 70°C

Parameter	Conditions	Min	Typ	Max	Units
Linear Sections					
Quiescent Current	BST=12V			5	mA
Output Voltage LDO1		2.493	2.525	2.556	V
Output Voltage LDO2		1.795	1.818	1.841	V
Gain (AOL)	LDOS (1,2) to GATE (1,2)		90		dB
Load Regulation	I_O = 0 to 8A			0.3	%
Line Regulation				0.3	%
Output Impedance	V_{GATE} = 6.5V		1	1.5	kΩ
BST Undervoltage Lockout			8.0		V
LDOEN Threshold		1.3		1.9	V
LDOEN Sink Current	LDOEN = 3.3V		0.01 -200	1.0 -300	µA µA
Overcurrent Trip Voltage	% of V_O Setpoint	20	40	60	%
Power-Up Output Short Circuit Immunity		1	5	60	ms
Output Short Circuit Glitch Immunity		0.5	4	6	ms
Gate Pulldown Impedance	GATE (1,2) - GND; VCC = BST = 0V	80	300	750	kΩ
VOSENSE Input Impedance		10			kΩ

Pin Configuration



Ordering Information

Device [1]	Package	Linear Voltage	Temp Range (T_J)
SC1188CS	SO-16	1.8V/2.5V	0° to 125°C

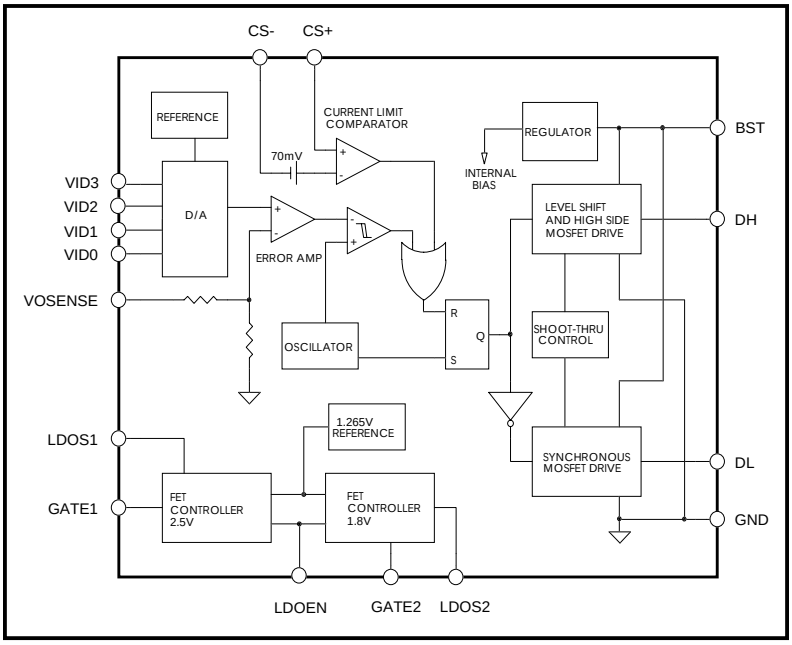
Note:
(1) Add suffix 'TR' for tape and reel.

Pin Descriptions

Pin #	Pin Name	Pin Function
1	GATE2	Gate Drive Output LDO2
2	GATE1	Gate Drive Output LDO1
3	LDOS1	Sense Input for LDO1
4	LDOS2	Sense Input for LDO2
5	LDOEN	3.3V Qualification for LDO1 & 2
6	CS -	Current Sense Input (negative)
7	CS+	Current Sense Input (positive)
8	GND	Power and Analog Ground
9	DL	Low Side Driver Output
10	DH	High Side Driver Output
11	BST	Supply for all IC circuits
12	VOSENSE	Top end of Internal Feedback Chain
13	VID3[1]	Programming Input (MSB)
14	VID2[1]	Programming Input
15	VID1[1]	Programming Input
16	VID0[1]	Programming Input (LSB)

Note:
(1) All logic level inputs and outputs are open collector TTL compatible.

Block Diagram



Applications Information - Output Voltage Table

Unless specified: V_{CC} = 3.13V to 3.47V; GND = P_{GND} = 0V; V_{OSENSE} = V_O; 0mV < (CS+-CS-) < 60mV; BST = 11.4V to 12.6V; T_A = 0 to 70°C

Parameter	Conditions	VID 3210	Min.	Typ.	Max.	Units
Output Voltage	I_O = 2A in Evaluation Board	1111	1.287	1.300	1.313	V
		1110	1.336	1.350	1.364	
		1101	1.386	1.400	1.414	
		1100	1.435	1.450	1.465	
		1011	1.485	1.500	1.515	
		1010	1.534	1.550	1.566	
		1001	1.584	1.600	1.616	
		1000	1.633	1.650	1.667	
		0111	1.683	1.700	1.717	
		0110	1.732	1.750	1.786	
		0101	1.782	1.800	1.818	
		0100	1.831	1.850	1.869	
		0011	1.881	1.900	1.919	
		0010	1.930	1.950	1.970	
		0001	1.980	2.000	2.020	
		0000	2.029	2.050	2.071	

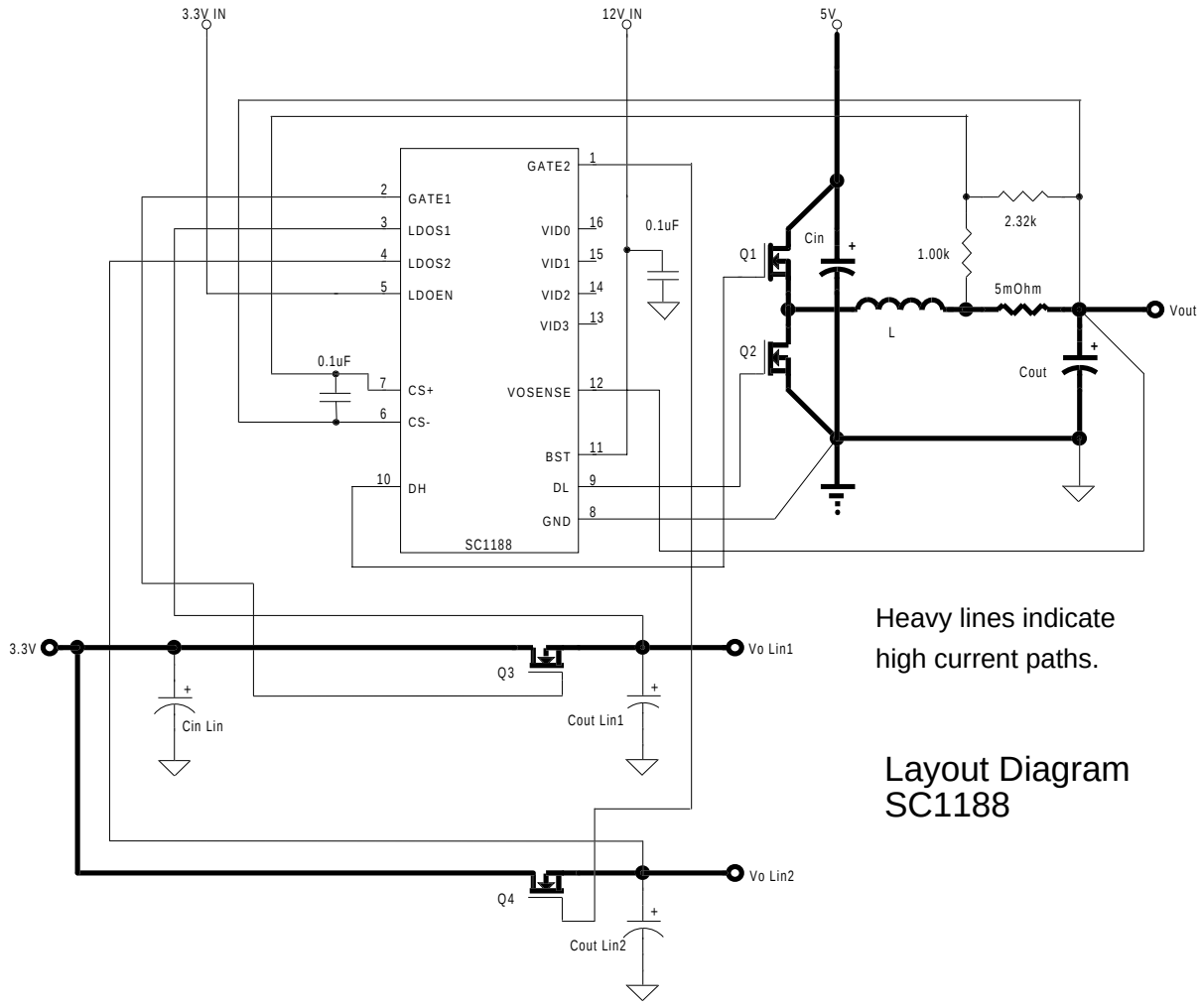
Layout Guidelines

Careful attention to layout requirements are necessary for successful implementation of the SC1188 PWM controller. High currents switching at 200kHz are present in the application and their effect on ground plane voltage differentials must be understood and minimized.

1). The high power parts of the circuit should be laid out first. A ground plane should be used, the number and position of ground plane interruptions should be such as to not unnecessarily compromise ground plane integrity. Isolated or semi-isolated areas of the ground plane may be deliberately introduced to constrain ground currents to particular areas, for example the input capacitor and bottom FET ground.

2). The loop formed by the Input Capacitor(s) (Cin), the Top FET (Q1) and the Bottom FET (Q2) must be kept as small as possible. This loop contains all the high current, fast transition switching. Connections should be as wide and as short as possible to minimize loop inductance. Minimizing this loop area will a) reduce EMI, b) lower ground injection currents, resulting in electrically "cleaner" grounds for the rest of the system and c) minimize source ringing, resulting in more reliable gate switching signals.

3). The connection between the junction of Q1, Q2 and the output inductor should be a wide trace or copper region. It should be as short as practical. Since this connection has fast voltage transitions, keeping this connection short will minimize EMI. The connection between the output inductor and the sense resistor should be a wide trace or copper area, there are no fast voltage or current transitions in this connection and length is not so important, however adding unnecessary impedance will reduce efficiency.



Layout Guidelines (Cont.)

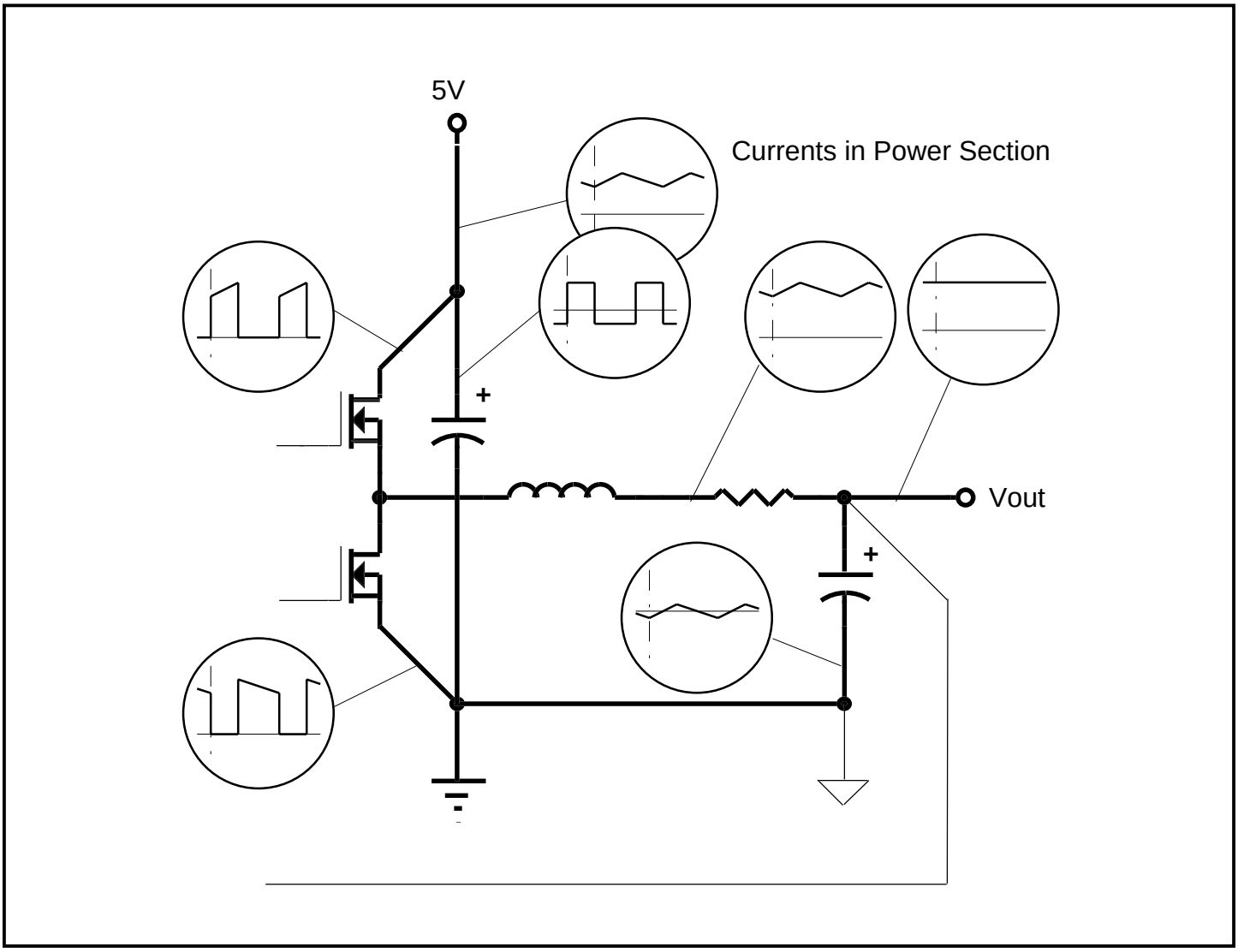
4) The Output Capacitor(s) (Cout) should be located as close to the load as possible, fast transient load currents are supplied by Cout only, and connections between Cout and the load must be short, wide copper areas to minimize inductance and resistance.

5) The SC1188 is best placed over a quiet ground plane area, avoid pulse currents in the Cin, Q1, Q2 loop flowing in this area. GND should be returned to the ground plane close to the package and close to the ground side of (one of) the output capacitor(s). If this is not possible, the GND pin may be connected to the ground path between the Output Capacitor(s) and the Cin, Q1, Q2 loop. Under no circumstances should GND be returned to a ground inside the Cin, Q1, Q2 loop.

6) BST for the SC1188 should be supplied from the 12V supply, the BST pin should be decoupled directly to GND by a 0.1mF ceramic capacitor, trace lengths should be as short as possible. The SC1188 Internal circuits are powered from this pin.

7) The Current Sense resistor and the divider across it should form as small a loop as possible, the traces running back to CS+ and CS- on the SC1188 should run parallel and close to each other. The 0.1µF capacitor should be mounted as close to the CS+ and CS- pins as possible.

8) Ideally, the grounds for the two LDO sections should be returned to the ground side of (one of) the output capacitor(s).



Component Selection

SWITCHING SECTION

OUTPUT CAPACITORS - Selection begins with the most critical component. Because of fast transient load current requirements in modern microprocessor core supplies, the output capacitors must supply all transient load current requirements until the current in the output inductor ramps up to the new level. Output capacitor ESR is therefore one of the most important criteria. The maximum ESR can be simply calculated from:

$$R_{ESR} \leq \frac{V_t}{I_t}$$

Where

V_t = Maximum transient voltage excursion

I_t = Transient current step

For example, to meet a 100mV transient limit with a 10A load step, the output capacitor ESR must be less than 10mW. To meet this kind of ESR level, there are three available capacitor technologies.

Technology	Each Cap.		Qty. Rqd.	Total	
	C (µF)	ESR (mΩ)		C (µF)	ESR (mΩ)
Low ESR Tantalum	330	60	6	2000	10
OS-CON	330	25	3	990	8.3
Low ESR Aluminum	1500	44	5	7500	8.3

The choice of which to use is simply a cost/performance issue, with Low ESR Aluminum being the cheapest, but taking up the most space.

INDUCTOR - Having decided on a suitable type and value of output capacitor, the maximum allowable value of inductor can be calculated. Too large an inductor will produce a slow current ramp rate and will cause the output capacitor to supply more of the transient load current for longer - leading to an output voltage sag below the ESR excursion calculated above.

The maximum inductor value may be calculated from:

$$L \leq \frac{R_{ESR}\, C}{I_t} \cdot V_A$$

where V_A is the lesser of V_O or $(V_{IN} - V_O)$

The calculated maximum inductor value assumes 100% and 0% duty cycle capability, so some allowance must be made. Choosing an inductor value of 50 to 75% of the calculated maximum will guarantee that the inductor current will ramp fast enough to reduce the voltage dropped across the ESR at a faster rate than the capacitor sags, hence ensuring a good recovery from transient with no additional excursions.

We must also be concerned with ripple current in the output inductor and a general rule of thumb has been to allow 10% of maximum output current as ripple current. Note that most of the output voltage ripple is produced by the inductor ripple current flowing in the output capacitor ESR. Ripple current can be calculated from:

$$I_{L_{RIPPLE}} = \frac{V_{IN}}{4 \cdot L \cdot f_{OSC}}$$

Ripple current allowance will define the minimum permitted inductor value.

POWER FETS - The FETs are chosen based on several criteria, with probably the most important being power dissipation and power handling capability.

TOP FET - The power dissipation in the top FET is a combination of conduction losses, switching losses and bottom FET body diode recovery losses.

a) Conduction losses are simply calculated as:

$$P_{COND} = I_O^2 \cdot R_{DS(on)} \cdot \delta$$

where

$$\delta = \text{duty cycle} \approx \frac{V_O}{V_{IN}}$$

b) Switching losses can be estimated by assuming a switching time, if we assume 100ns then:

$$P_{SW} = I_O \cdot V_{IN} \cdot 10^{-2}$$

or more generally,

$$P_{SW} = \frac{I_O \cdot V_{IN} \cdot (t_r + t_f) \cdot f_{OSC}}{4}$$

c) Body diode recovery losses are more difficult to estimate, but to a first approximation, it is reasonable to assume that the stored charge on the bottom FET body diode will be moved through the top FET as it starts to turn on. The resulting power dissipation in the top FET will be:

$$P_{RR} = Q_{RR} \cdot V_{IN} \cdot f_{OSC}$$

To a first order approximation, it is convenient to only consider conduction losses to determine FET suitability. For a 5V in; 2.8V out at 14.2A requirement, typical FET losses would be:

Component Selection (Cont.)

Using 1.5X Room temp $R_{DS(ON)}$ to allow for temperature rise.

FET type	$R_{DS(on)}$ (mΩ)	P_D (W)	Package
IRL34025	15	1.69	D²Pak
IRL2203	10.5	1.19	D²Pak
Si4410	20	2.26	S0-8

BOTTOM FET - Bottom FET losses are almost entirely due to conduction. The body diode is forced into conduction at the beginning and end of the bottom switch conduction period, so when the FET turns on and off, there is very little voltage across it, resulting in low switching losses. Conduction losses for the FET can be determined by:

$$P_{COND} = I_O^2 \cdot R_{DS(on)} \cdot (1-\delta)$$

For the example above:

FET type	$R_{DS(on)}$ (mΩ)	P_D (W)	Package
IRL34025	15	1.33	D²Pak
IRL2203	10.5	0.93	D²Pak
Si4410	20	1.77	S0-8

Each of the package types has a characteristic thermal impedance. For the surface mount packages on double sided FR4, 2 oz printed circuit board material, thermal impedances of 40°C/W for the D²PAK and 80°C/W for the SO-8 are readily achievable. The corresponding temperature rise is detailed below:

	Temperature Rise (°C)	
FET type	Top FET	Bottom FET
IRL34025	67.6	53.2
IRL2203	47.6	37.2
Si4410	180.8	141.6

It is apparent that single SO-8 Si4410 are not adequate for this application, but by using parallel pairs in each position, power dissipation will be approximately halved and temperature rise reduced by a factor of 4.

INPUT CAPACITORS - since the RMS ripple current in the input capacitors may be as high as 50% of the output current, suitable capacitors must be chosen accordingly. Also, during fast load transients, there may be restrictions on input di/dt. These restrictions require useable energy storage within the converter circuitry, either as extra output capacitance or, more usually, additional input capacitors. Choosing low ESR input capacitors will help maximize ripple rating for a given size.

SHORT CIRCUIT PROTECTION - LINEARS

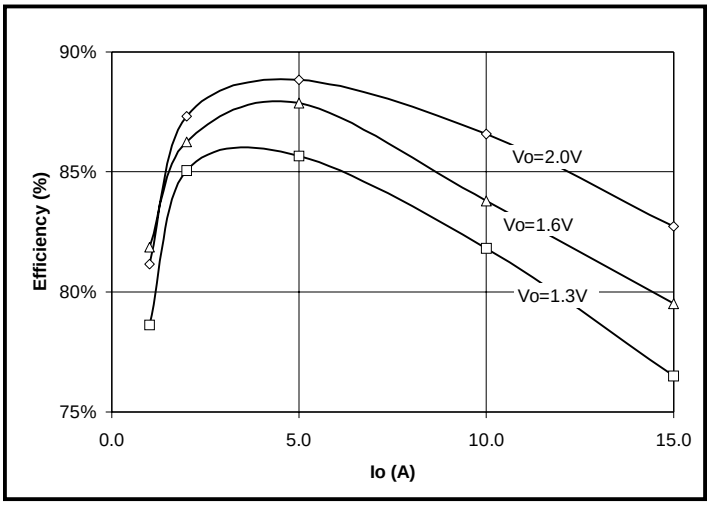
The Short circuit feature on the linear controllers is implemented by using the Rds(on) of the FETs. As output current increases, the regulation loop maintains the output voltage by turning the FET on more and more. Eventually, as the Rds(on) limit is reached, the FET will be unably to turn on more fully, and output voltage will start to fall. When the output voltage falls to approximately 50% of nominal, the LDO controller is latched off, setting output voltage to 0. Power must be cycled to reset the latch.

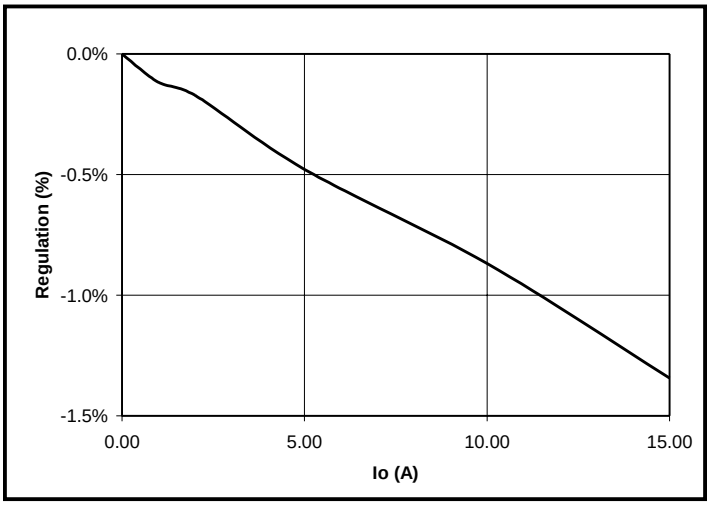
To prevent false latching due to capacitor inrush currents or low supply rails, the current limit latch is initially disabled. It is enabled at a preset time (nominally 2ms) after both the VCC and BST rails rise above their lockout points. To be most effective, the linear FET Rds(on) should not be selected artificially low, the FET should be chosen so that, at maximum required current, it is almost fully turned on. If, for example, a linear supply of 1.5V at 4A is required from a 3.3V ± 5% rail, max allowable Rds(on) would be.

Rds(on)max = (0.95*3.3-1.5)/4 » 400mΩ

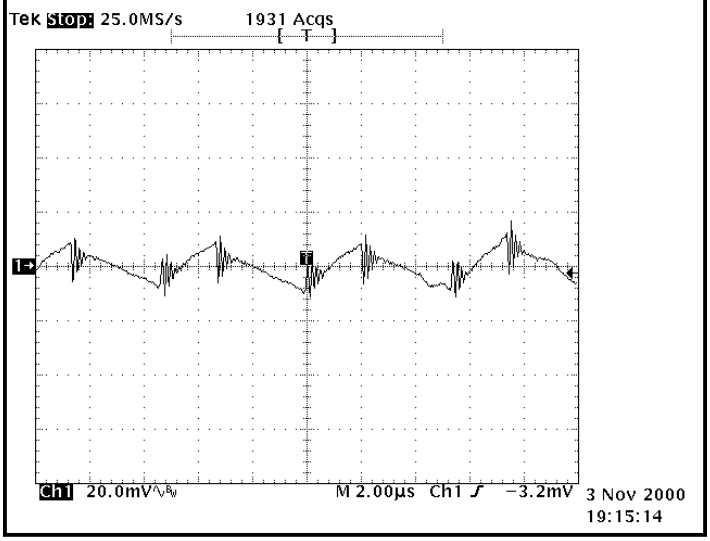
To allow for temperature effects 200mΩ would be a suitable room temperature maximum, allowing a peak short circuit current of approximately 15A for a short time before shutdown.

Typical Characteristics

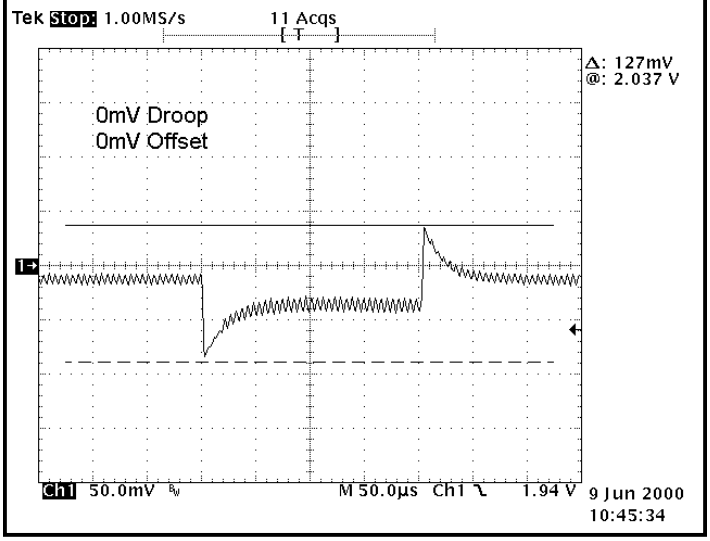




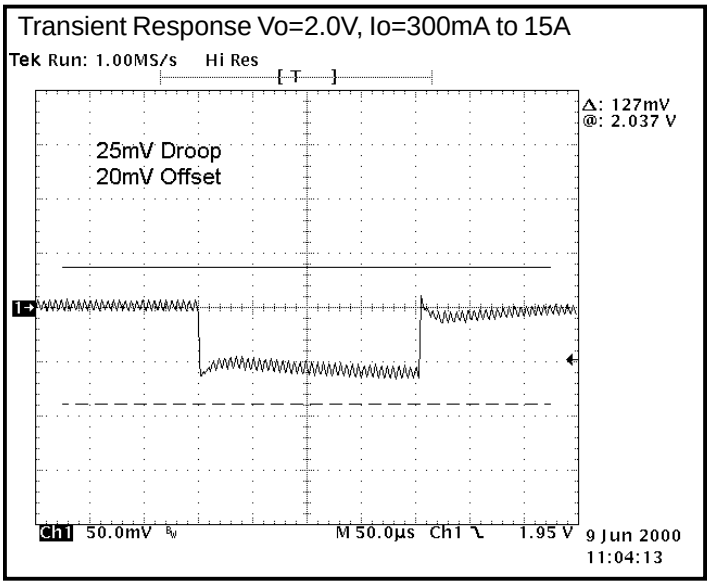
Ripple Voltage, Vo=1.6V; Io=15A



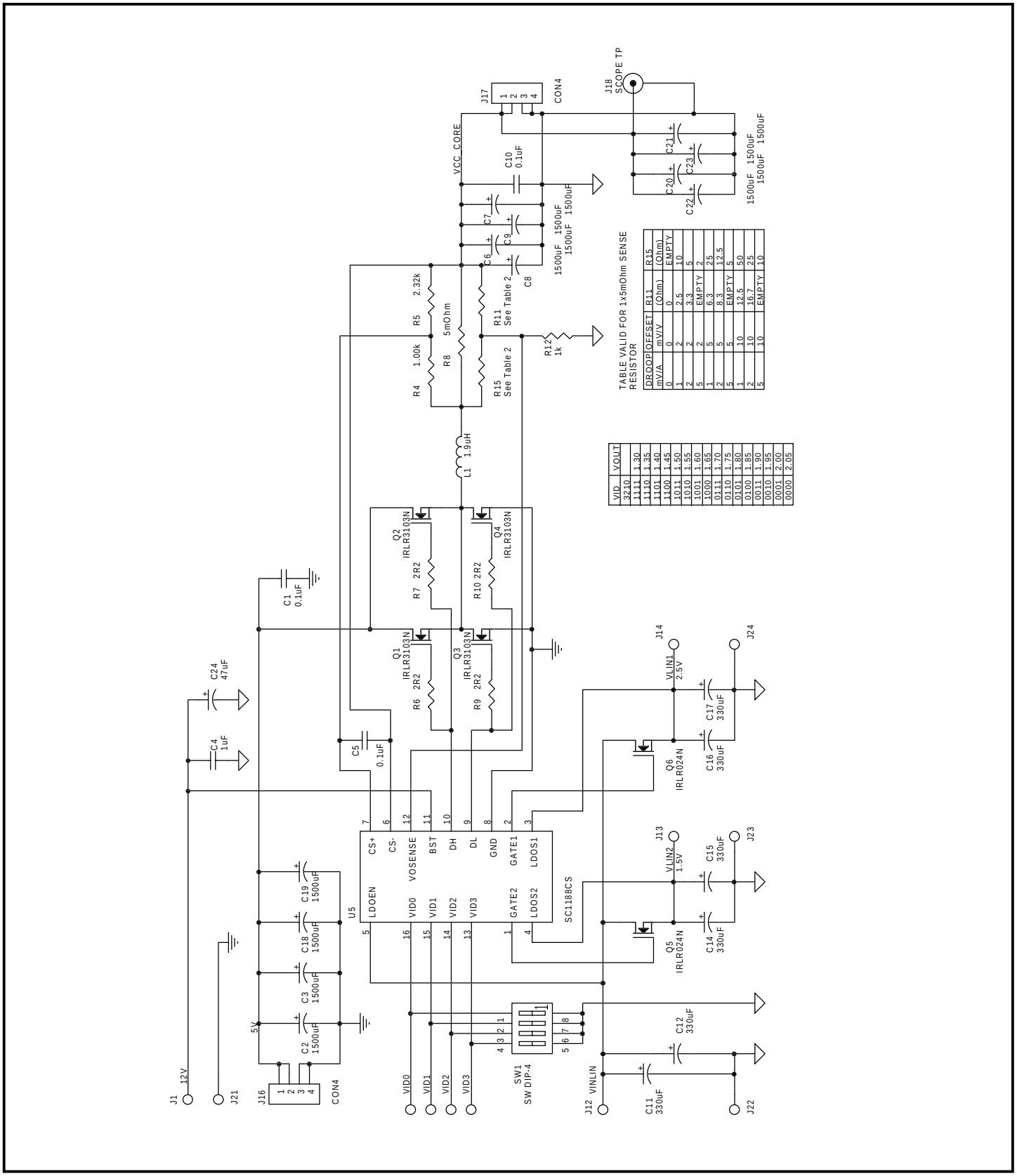
Transient Response Vo=2.0V, Io=300mA to 15A



Transient Response Vo=2.0V, Io=300mA to 15A



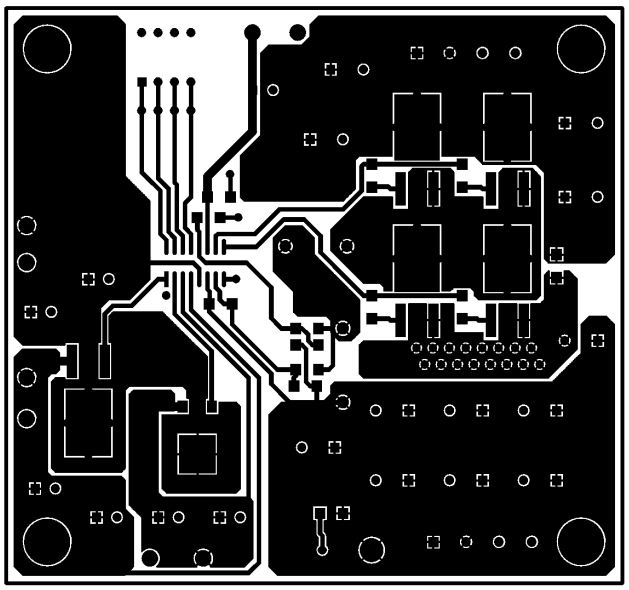
Evaluation Board Schematic



Evaluation Board Bill of Materials

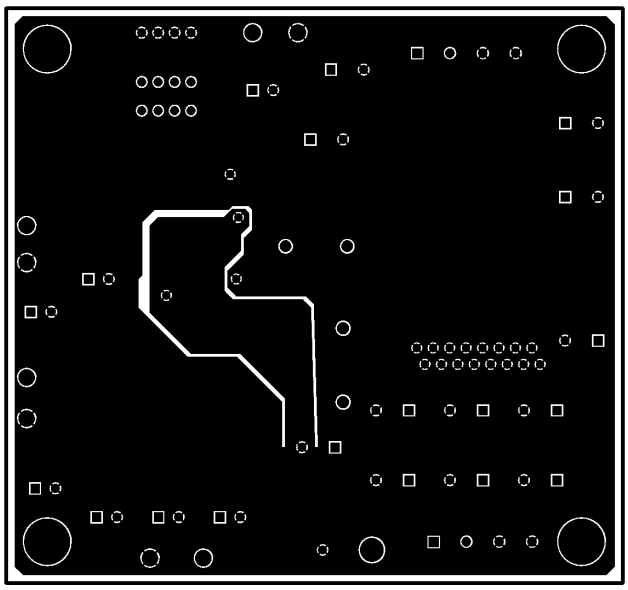
	Qty.	Reference	Value	Notes
1	4	C1, C5, C10	0.1µF	
2	12	C2, C3, C6, C7, C8, C9, C18, C19, C20, C21, C22, C23	1500µF	Low ESR Sanyo MV-GX or equivalent
	1	C4	1µF	Ceramic
3	6	C11, C12, C14, C15, C16, C17	330µF	
	1	C24	47µF	
4	1	L1	1.9µH	
5	4	Q1, Q2, Q3, Q4	IRLR3103N	
6	2	Q5, Q6	IRLR024N	
7	1	R4	1.00k	1%
8	1	R5	2.32k	1%
9	4	R6, R7, R9 R10	2R2	
10	1	R8	5mOhm	IRC OAR1
11	2	R15, R11	See Table	
12	1	R12	1k	
13	1	SW1	SW DIP-4	
14	1	U4	SC1188CS	SEMTECH

Evaluation Board Gerber Plots



TOP COPPER

SEMTECH
SC1188 EVAL BD.
REV 2.1



BOTTOM COPPER

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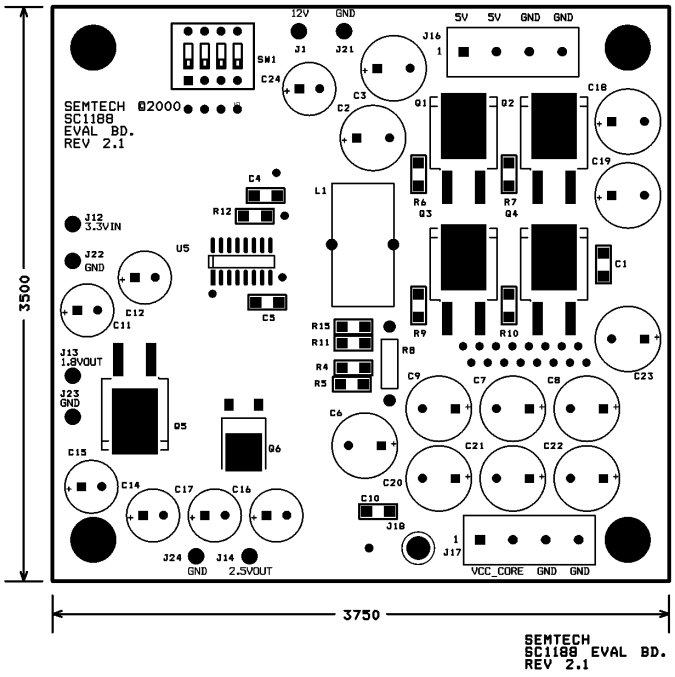
SC1188 EVAL BD.
REV 2.1



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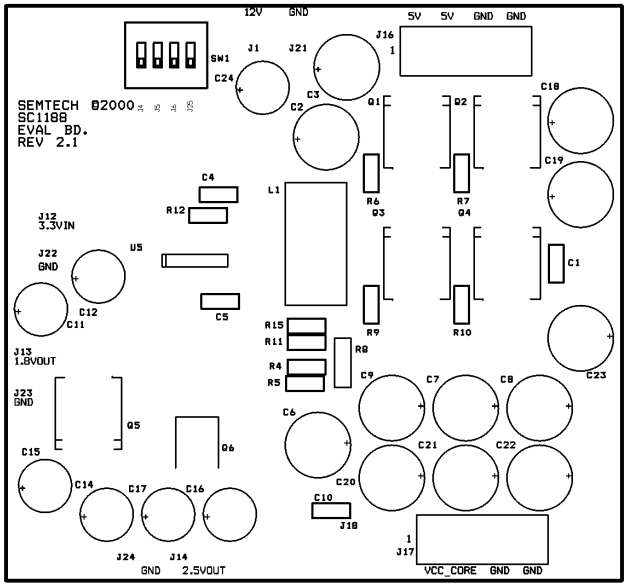
SC1188 EVAL BD.
REV 2.1

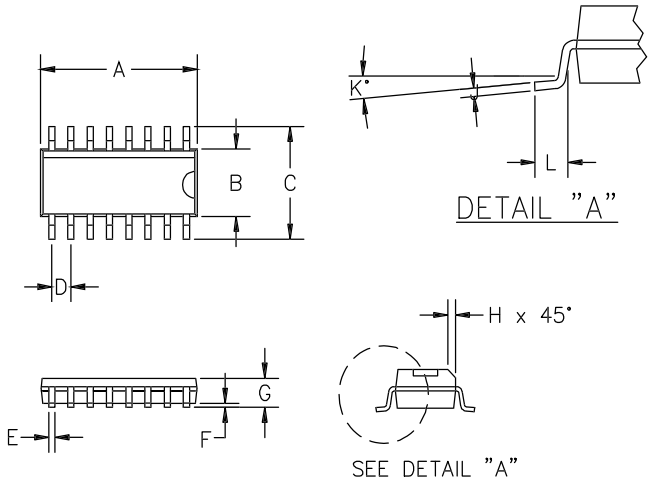
SILK SCREEN TOP
ASSEMBLY TOP



SEMTECH
SC1188 EVAL BD.
REV 2.1

SILK SCREEN TOP

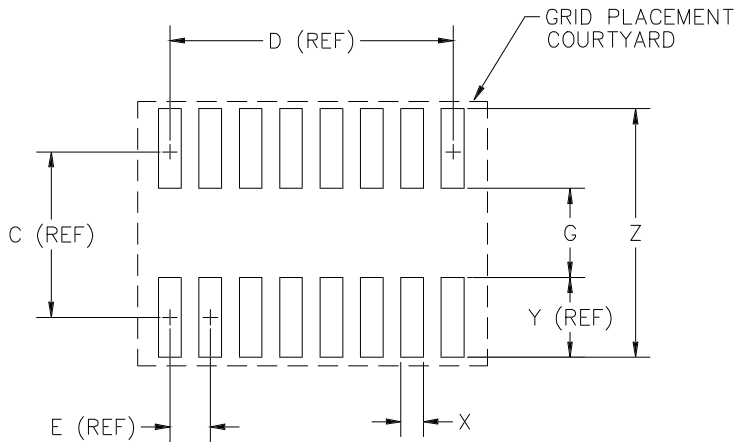
Outline Drawing - SO-16



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.386	.393	9.80	10.0	[2]
B	.150	.158	3.80	4.00	[2]
C	.228	.244	5.80	6.20	–
D	.050	BSC	1.27	BSC	–
E	.013	.020	0.33	0.51	–
F	.004	.010	.10	.25	–
G	.053	.069	1.35	1.75	–
H	.010	.020	.25	.50	–
J	.007	.010	.19	.25	–
K	0°	8°	0°	8°	–
L	.016	.050	.40	1.27	–

[2] DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTUSIONS

Land Pattern - SO-16



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
C	–	.197	–	5.00	–
D	–	.35	–	8.89	–
E	–	.05	–	1.27	–
G	.102	.110	2.60	2.80	–
X	.02	.03	.60	.80	–
Y	–	.095	–	2.40	–
Z	.28	.29	7.20	7.40	–

[1] GRID PLACEMENT COURTYARD IS 22 X 16 ELEMENTS (11mm X 8mm) IN ACCORDANCE WITH THE INTERNATIONAL GRID DETAILED IN IEC PUBLICATION 97.

Contact Information

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